

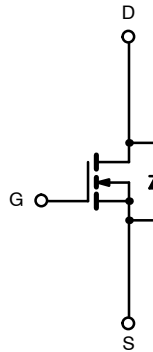
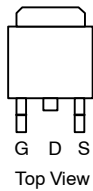


N-Channel 150-V (D-S) 175°C MOSFET

PRODUCT SUMMARY

| $V_{(BR)DSS}$ (V) | $r_{DS(on)}$ (Ω) | I_D (A) |
|-------------------|---------------------------|-----------------|
| 150 | 0.019 @ $V_{GS} = 10$ V | 85 ^a |

TO-263



FEATURES

- TrenchFET® Power MOSFET
- 175°C Junction Temperature
- New Low Thermal Resistance Package
- 100% R_g Tested

APPLICATIONS

- Primary Side Switch
- Automotive
 - 42-V EPS and ABS
 - DC/DC Conversion
 - Motor Drives

Ordering Information: SUM85N15-19
SUM85N15-19-E3 (Lead Free)

N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

| Parameter | Symbol | Limit | Unit | |
|--|----------------|---------------------------------------|--------------------------|----|
| Drain-Source Voltage | V_{DS} | 150 | V | |
| Gate-Source Voltage | V_{GS} | ± 20 | | |
| Continuous Drain Current ($T_J = 175^\circ\text{C}$) | I_D | $T_C = 25^\circ\text{C}$ | 85 ^a | |
| | | $T_C = 125^\circ\text{C}$ | 50 ^a | |
| Pulsed Drain Current | I_{DM} | 180 | A | |
| Avalanche Current | I_{AR} | 50 | | |
| Repetitive Avalanche Energy ^b | E_{AR} | $L = 0.1$ mH | 125 | mJ |
| Maximum Power Dissipation ^b | | | $T_C = 25^\circ\text{C}$ | |
| | | $T_A = 25^\circ\text{C}$ ^d | 3.75 | W |
| Operating Junction and Storage Temperature Range | T_J, T_{stg} | -55 to 175 | $^\circ\text{C}$ | |

THERMAL RESISTANCE RATINGS

| Parameter | Symbol | Limit | Unit |
|--------------------------|------------|-------|--------------------|
| Junction-to-Ambient | R_{thJA} | 40 | $^\circ\text{C/W}$ |
| Junction-to-Case (Drain) | | | |

Notes

- Package limited.
- Duty cycle $\leq 1\%$.
- See SOA curve for voltage derating.
- When mounted on 1" square PCB (FR-4 material).

| SPECIFICATIONS ($T_J = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED) | | | | | | |
|---|---------------|--|-----|-------|-----------|---------------|
| Parameter | Symbol | Test Condition | Min | Typ | Max | Unit |
| Static | | | | | | |
| Drain-Source Breakdown Voltage | $V_{(BR)DSS}$ | $V_{DS} = 0\text{ V}, I_D = 250\ \mu\text{A}$ | 150 | | | V |
| Gate-Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$ | 2 | | 4 | V |
| Gate-Body Leakage | I_{GSS} | $V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$ | | | ± 100 | nA |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = 150\text{ V}, V_{GS} = 0\text{ V}$ | | | 1 | μA |
| | | $V_{DS} = 150\text{ V}, V_{GS} = 0\text{ V}, T_J = 125^\circ\text{C}$ | | | 50 | |
| | | $V_{DS} = 150\text{ V}, V_{GS} = 0\text{ V}, T_J = 175^\circ\text{C}$ | | | 250 | |
| On-State Drain Current ^a | $I_{D(on)}$ | $V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$ | 120 | | | A |
| Drain-Source On-State Resistance ^a | $r_{DS(on)}$ | $V_{GS} = 10\text{ V}, I_D = 30\text{ A}$ | | 0.015 | 0.019 | Ω |
| | | $V_{GS} = 10\text{ V}, I_D = 30\text{ A}, T_J = 125^\circ\text{C}$ | | | 0.038 | |
| | | $V_{GS} = 10\text{ V}, I_D = 30\text{ A}, T_J = 175^\circ\text{C}$ | | | 0.050 | |
| Forward Transconductance ^a | g_{fs} | $V_{DS} = 15\text{ V}, I_D = 30\text{ A}$ | 25 | | | S |
| Dynamic^b | | | | | | |
| Input Capacitance | C_{iss} | $V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$ | | 4750 | | μF |
| Output Capacitance | C_{oss} | | | 530 | | |
| Reverse Transfer Capacitance | C_{rss} | | | 220 | | |
| Total Gate Charge ^c | Q_g | $V_{DS} = 75\text{ V}, V_{GS} = 10\text{ V}, I_D = 85\text{ A}$ | | 76 | 110 | nC |
| Gate-Source Charge ^c | Q_{gs} | | | 21 | | |
| Gate-Drain Charge ^c | Q_{gd} | | | 26 | | |
| Gate Resistance | R_g | | 0.5 | 1.8 | 3.0 | Ω |
| Turn-On Delay Time ^c | $t_{d(on)}$ | $V_{DD} = 75\text{ V}, R_L = 0.9\ \Omega$ $I_D \cong 85\text{ A}, V_{GEN} = 10\text{ V}, R_g = 2.5\ \Omega$ | | 22 | 35 | ns |
| Rise Time ^c | t_r | | | 170 | 250 | |
| Turn-Off Delay Time ^c | $t_{d(off)}$ | | | 40 | 60 | |
| Fall Time ^c | t_f | | | 170 | 250 | |
| Source-Drain Diode Ratings and Characteristics ($T_C = 25^\circ\text{C}$)^b | | | | | | |
| Continuous Current | I_S | | | | 85 | A |
| Pulsed Current | I_{SM} | | | | 180 | |
| Forward Voltage ^a | V_{SD} | $I_F = 85\text{ A}, V_{GS} = 0\text{ V}$ | | 1.0 | 1.5 | V |
| Reverse Recovery Time | t_{rr} | $I_F = 50\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$ | | 130 | 200 | ns |
| Peak Reverse Recovery Current | $I_{RM(REC)}$ | | | 8 | 12 | A |
| Reverse Recovery Charge | Q_{rr} | | | 0.52 | 1.2 | μC |

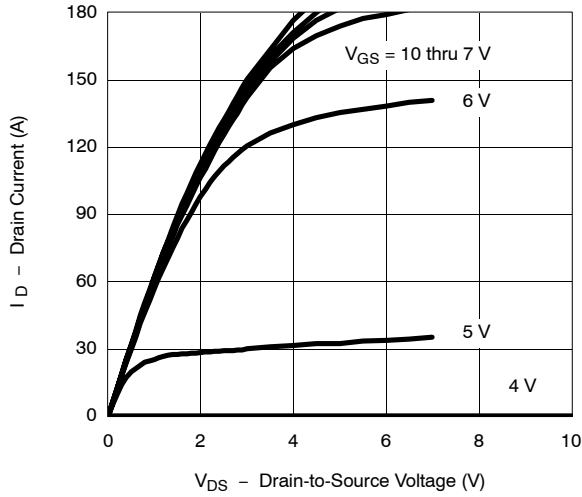
Notes

- a. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

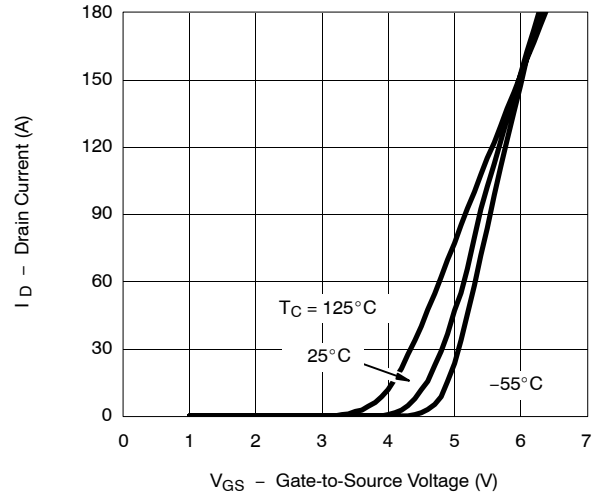


TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)

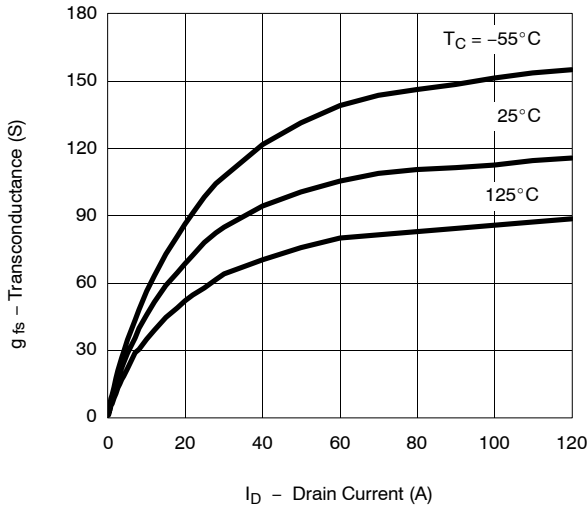
Output Characteristics



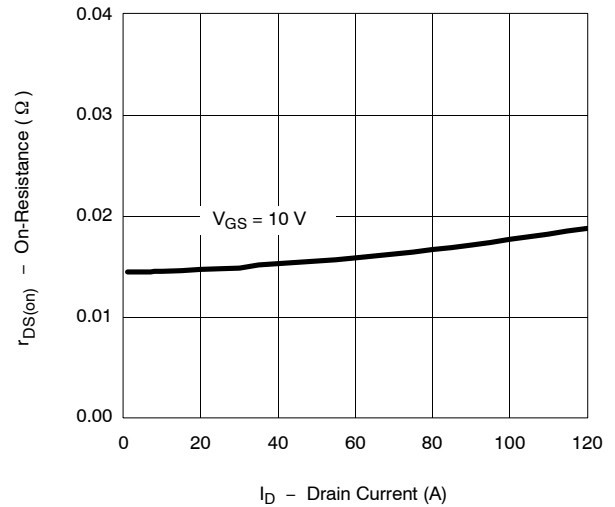
Transfer Characteristics



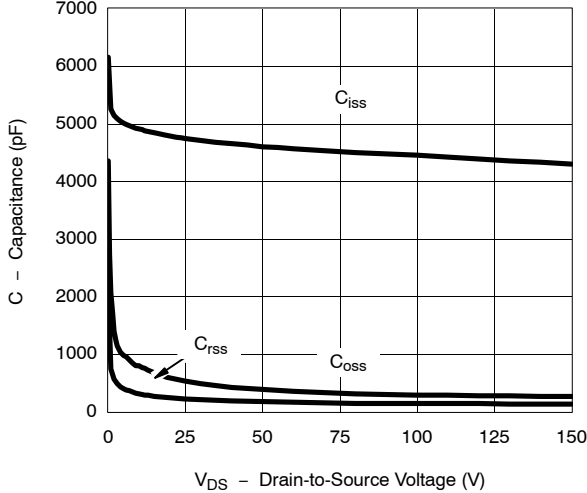
Transconductance



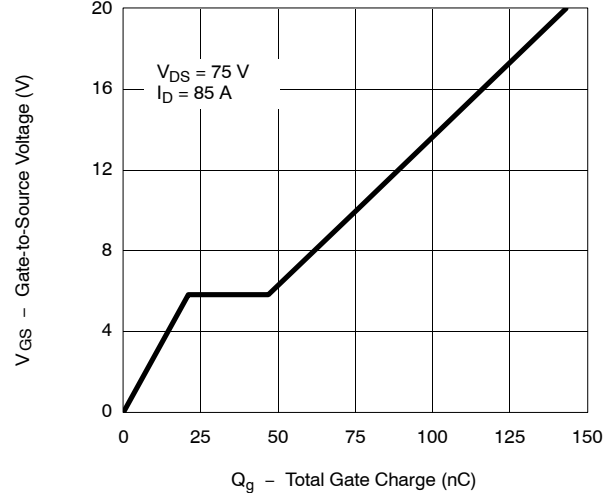
On-Resistance vs. Drain Current



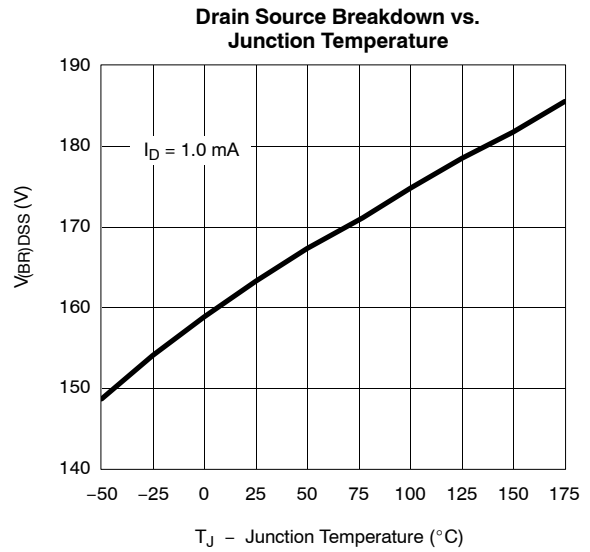
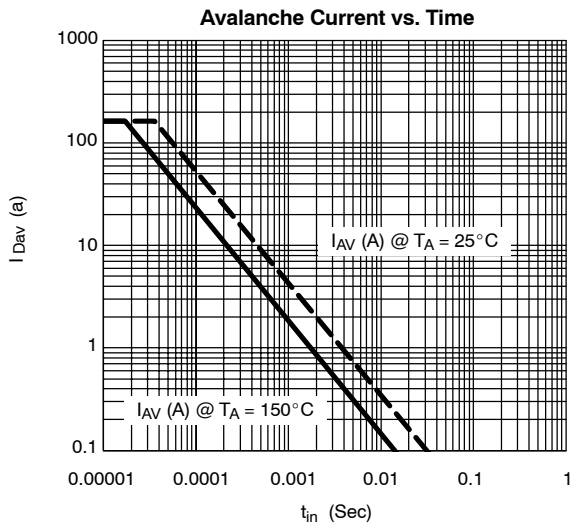
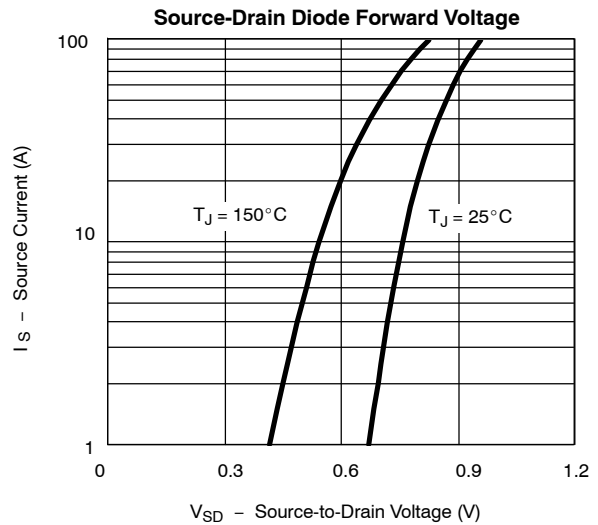
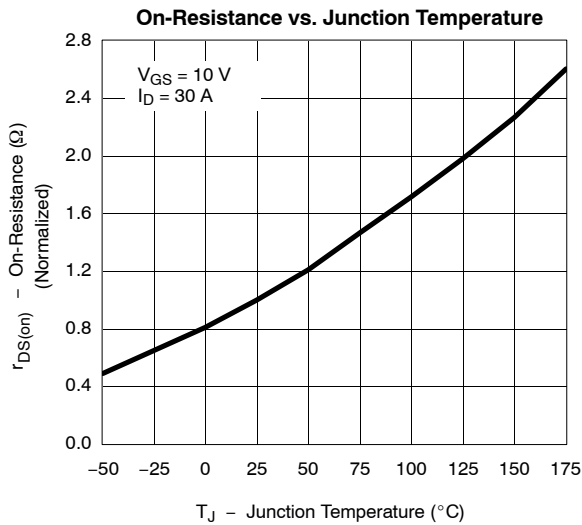
Capacitance



Gate Charge

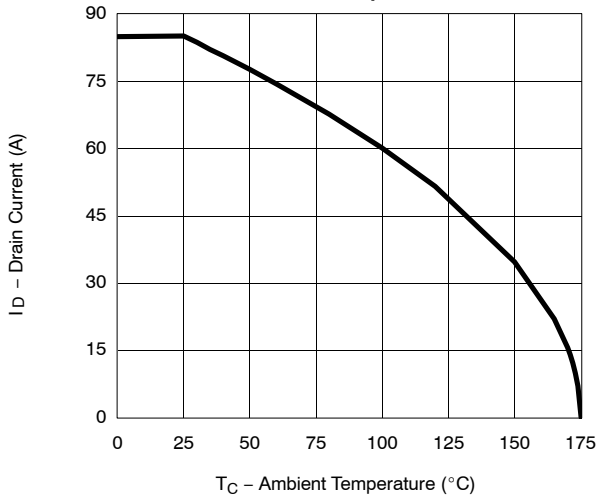


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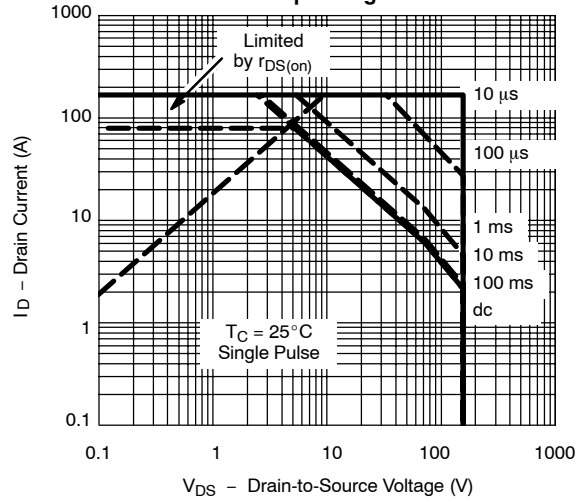


THERMAL RATINGS

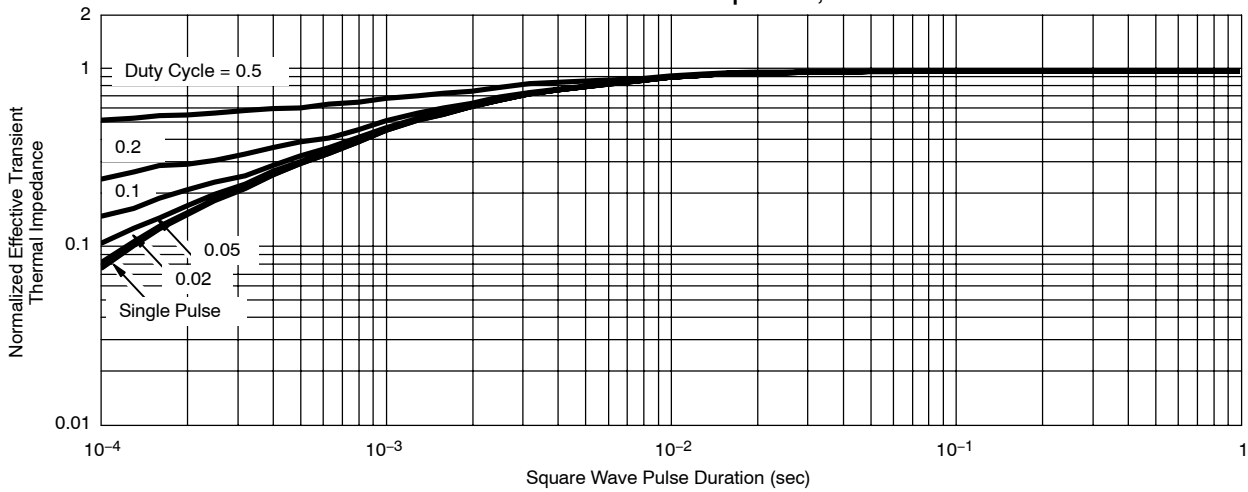
Maximum Avalanche and Drain Current vs. Case Temperature



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case





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